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Should be replaced with:

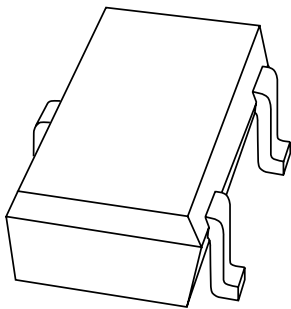
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If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DATA SHEET



BC859W; BC860W PNP general purpose transistors

Product data sheet
Supersedes data of 1997 Sep 03

1999 Apr 12

PNP general purpose transistors

BC859W; BC860W

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 45 V).

APPLICATIONS

- Low noise stages in tape recorders, hi-fi amplifiers and other audio-frequency equipment.

DESCRIPTION

PNP transistor in a SOT323 plastic package.
NPN complements: BC849W and BC850W.

MARKING

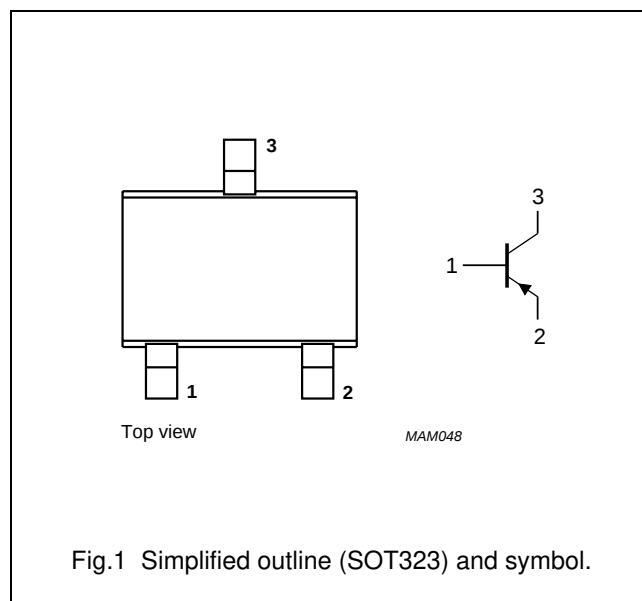
TYPE NUMBER	MARKING CODE	TYPE NUMBER	MARKING CODE
BC859W	4D*	BC860W	4H*
BC859BW	4B*	BC860BW	4F*
BC859CW	4C*	BC860CW	4G*

Note

- * = - : Made in Hong Kong.
* = t : Made in Malaysia.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter			
	BC859W		–	–30	V
	BC860W		–	–50	V
V_{CEO}	collector-emitter voltage	open base			
	BC859W		–	–30	V
	BC860W		–	–45	V
V_{EBO}	emitter-base voltage	open collector	–	–5	V
I_C	collector current (DC)		–	–100	mA
I_{CM}	peak collector current		–	–200	mA
I_{BM}	peak base current		–	–200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$; note 1	–	200	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

PNP general purpose transistors

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	625	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_{amb} = 25\text{ °C}$ unless otherwise specified.

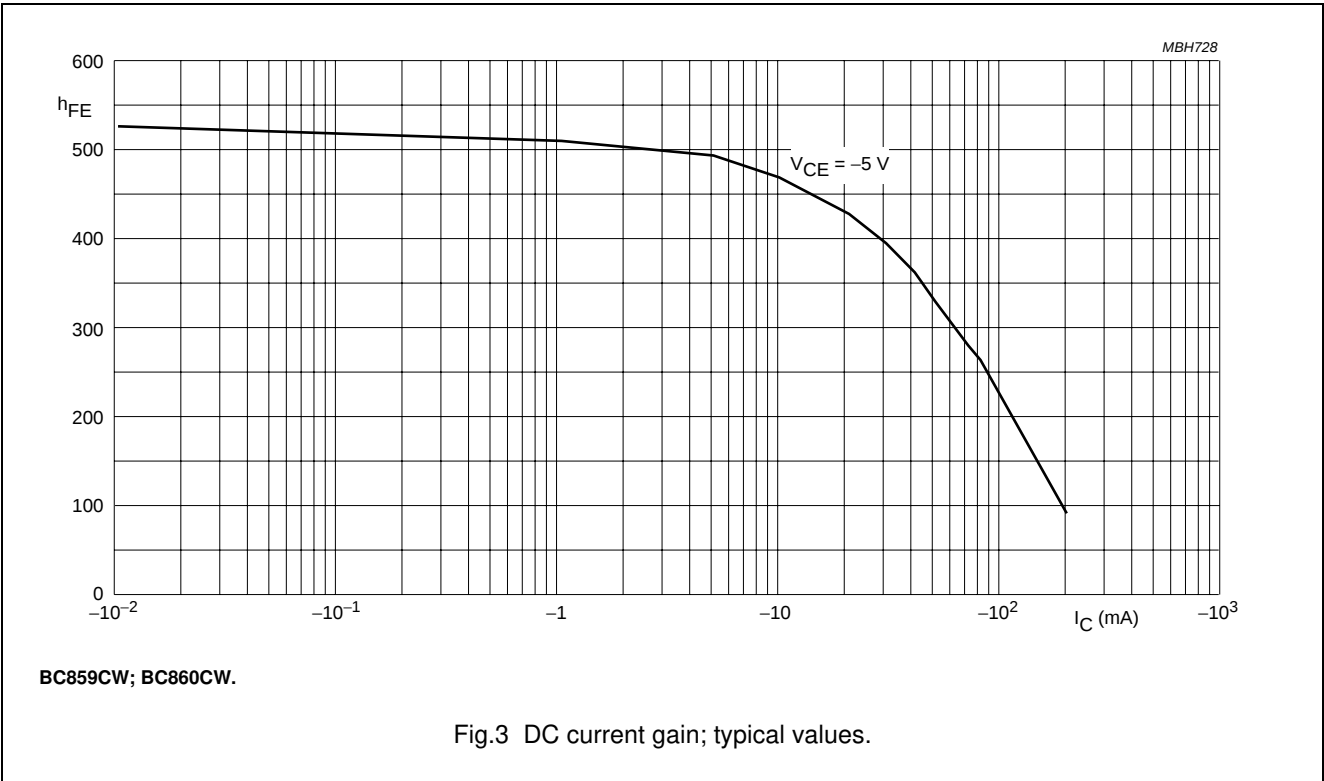
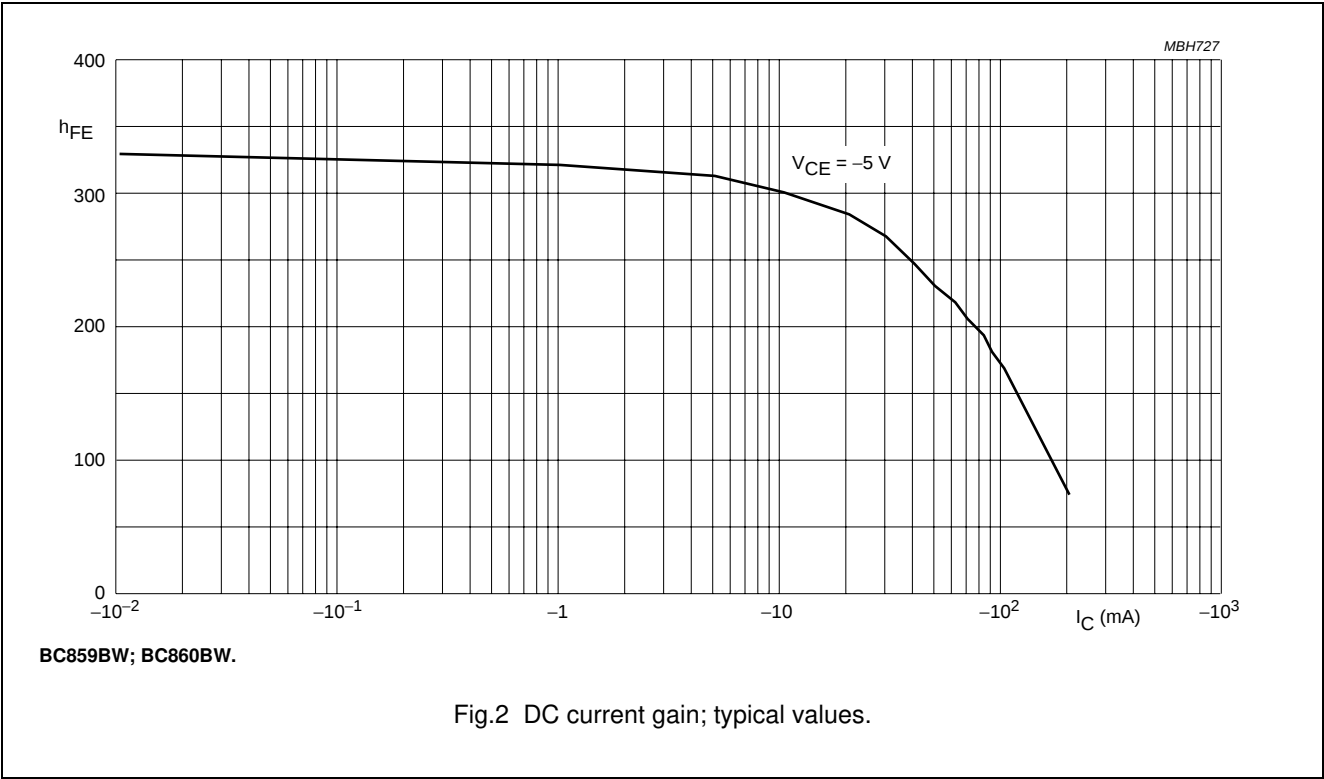
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0$; $V_{CB} = -30\text{ V}$	–	–	–15	nA
		$I_E = 0$; $V_{CB} = -30\text{ V}$; $T_j = 150\text{ °C}$	–	–	–4	μA
I_{EBO}	emitter cut-off current	$I_C = 0$; $V_{EB} = -5\text{ V}$	–	–	–100	nA
h_{FE}	DC current gain BC859W; BC860W BC859BW; BC860BW BC859CW; BC860CW	$I_C = -2\text{ mA}$; $V_{CE} = -5\text{ V}$; see Figs 2 and 3	220	–	800	
			220	–	475	
			420	–	800	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -10\text{ mA}$; $I_B = -0.5\text{ mA}$	–	–	–300	mV
		$I_C = -100\text{ mA}$; $I_B = -5\text{ mA}$; note 1	–	–	–650	mV
V_{BE}	base-emitter voltage	$I_C = -2\text{ mA}$; $V_{CE} = -5\text{ V}$	600	–	750	mV
		$I_C = -10\text{ mA}$; $V_{CE} = -5\text{ V}$	–	–	820	mV
C_c	collector capacitance	$I_E = I_B = 0$; $V_{CB} = -10\text{ V}$; $f = 1\text{ MHz}$	–	–	5	pF
C_e	emitter capacitance	$I_C = I_E = 0$; $V_{EB} = -500\text{ mV}$; $f = 1\text{ MHz}$	–	10	–	pF
f_T	transition frequency	$I_C = -10\text{ mA}$; $V_{CE} = -5\text{ V}$; $f = 100\text{ MHz}$	100	–	–	MHz
F	noise figure; BC859W; BC860W; BC859BW; BC860BW; BC859CW; BC860CW	$I_C = -200\text{ }\mu\text{A}$; $V_{CE} = -5\text{ V}$; $R_S = 2\text{ k}\Omega$; $f = 10\text{ Hz}$ to 15.7 kHz	–	–	4	dB
		$I_C = -200\text{ }\mu\text{A}$; $V_{CE} = -5\text{ V}$; $R_S = 2\text{ k}\Omega$; $f = 1\text{ kHz}$; $B = 200\text{ Hz}$	–	–	4	dB

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.

PNP general purpose transistors

BC859W; BC860W



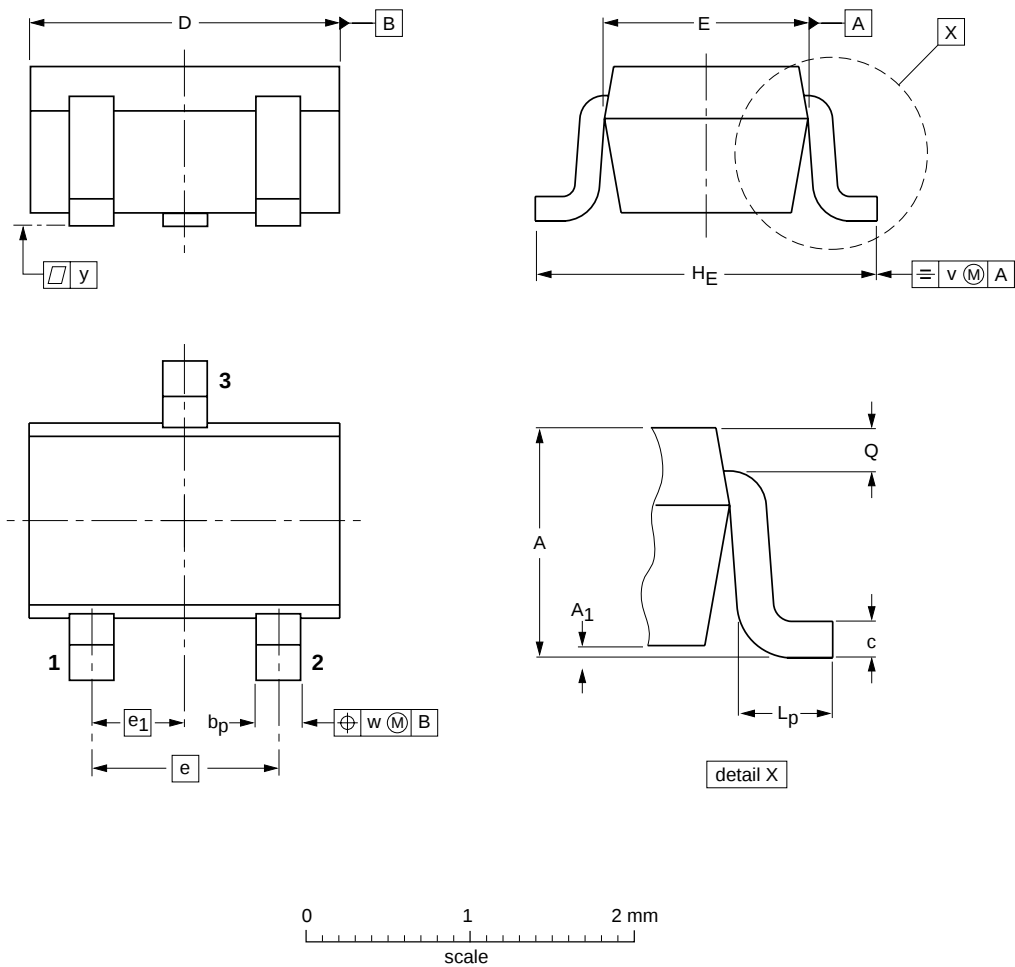
PNP general purpose transistors

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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT323



DIMENSIONS (mm are the original dimensions)

UNIT	A	A1 max	bp	c	D	E	e	e1	HE	Lp	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT323			SC-70			97-02-28

PNP general purpose transistors

BC859W; BC860W

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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NXP Semiconductors

Customer notification

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Contact information

For additional information please visit: **<http://www.nxp.com>**

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